

Silicon PNP Power Transistors

2SA914

DESCRIPTION

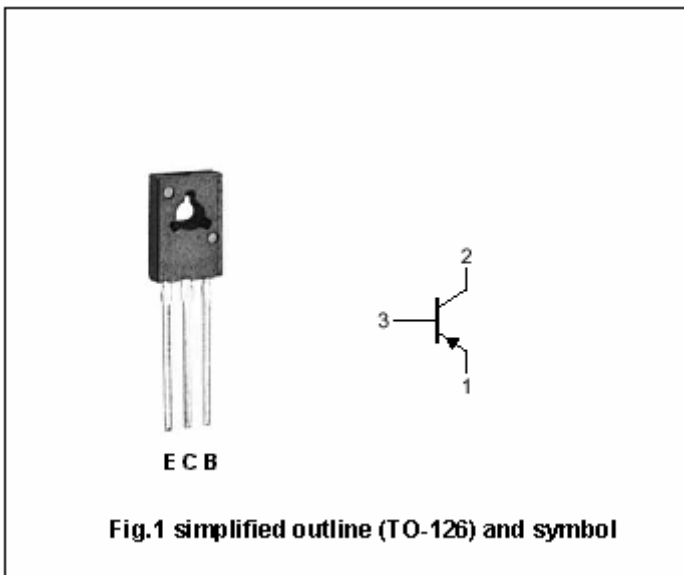
- With TO-126 package
- Complement to type 2SC1953
- Good linearity of h_{FE}
- High V_{CEO}

APPLICATIONS

- For audio frequency power pre-amplifier

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |



Absolute Maximun Ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| V_{CBO} | Collector-base voltage | Open emitter | -150 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -150 | V |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current | | -50 | mA |
| I_{CM} | Collector current-Peak | | -100 | mA |
| P_C | Collector power dissipation | | 1 | W |
| T_j | Junction temperature | | 150 | °C |
| T_{stg} | Storage temperature | | -55~150 | °C |

Silicon PNP Power Transistors

2SA914

CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-0.1mA; I _B =0 | -150 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =-10 μ A ; I _C =0 | -5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-30mA ; I _B =-3mA | | | -1.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-100V; I _E =0 | | | -1 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -1 | μ A |
| h _{FE} | DC current gain | I _C =-10mA ; V _{CE} =-5V | 90 | | 450 | |
| C _{OB} | Output capacitance | I _E =0 ; V _{CB} =-10V; f=1MHz | | | 5 | pF |
| f _T | Transition frequency | I _E =10mA ; V _{CB} =-10V | | 200 | | MHz |

◆ h_{FE} Classifications

| Q | R | S | T |
|--------|---------|---------|---------|
| 90-155 | 130-220 | 185-330 | 260-450 |

PACKAGE OUTLINE

